

ABSTRACT OF THE DISCLOSURE

A surface emitting semiconductor laser includes a substrate, a first mirror that is formed on the substrate and includes semiconductor layers of a first conduction type, a 5 second mirror that includes semiconductor layers of a second conduction type, an active region disposed between the first and second mirrors, a current confinement layer that is disposed between the first and second mirrors and includes a selectively oxidized region, and an inorganic insulation film. 10 A mesa structure includes at least the second mirror and the current confinement layer. The inorganic insulation film covers at least a side surface of the mesa structure and having an internal stress equal to or less than 1.5×10^9 dyne/cm².

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